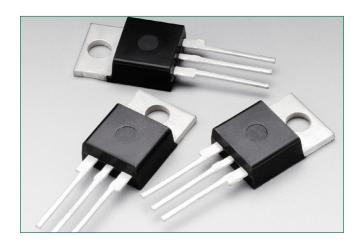
Surface Mount – 400V - 800V







#### **Additional Information**







Accessories



Samples

### **Description**

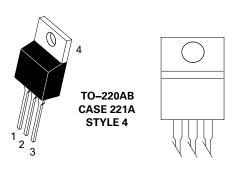
Designed primarily for full-wave ac control applications, such as motor controls, heating controls or dimmers; or wherever fullwave, silicon gate—controlled devices are needed.

#### **Features**

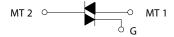
- Uniform Gate Trigger Currents in Three Quadrants, Q1, Q2, and Q3
- High Commutating di/dt and High Immunity to
- dv/dt @ 125°C
- Minimizes Snubber Networks for Protection
- Blocking Voltage to 800 Volts
- On-State Current Rating of 12 Amperes RMS at 80°C

- High Surge Current Capability100 Amperes
- Industry Standard TO-220AB Package for Ease of Design
- Glass Passivated Junctions for Reliability and Uniformity
- These Devices are Pb-Free and are RoHS Compliant

### **Pin Out**



### **Functional Diagram**



Surface Mount - 400V - 800V

### Maximum Ratings (TJ = 25°C unless otherwise noted)

Rating		Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1)		${ m V}_{ m DRM'}$	400 600 800	V
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, $T_c = 80$ °C)		I <sub>T (RMS)</sub>	12	А
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T <sub>c</sub> = 125°C)		I <sub>TSM</sub>	100	А
Circuit Fusing Consideration (t = 8.3 ms)		l²t	41	A²sec
Peak Gate Power (Pulse Width $\leq$ 1.0 $\mu$ s, $T_{C}$ = 80°C)		$P_{GM}$	16	W
Average Gate Power (t = $8.3 \text{ ms}$ , $T_c = 80^{\circ}\text{C}$ )		P <sub>G(AV)</sub>	0.35	W
Operating Junction Temperature Range		$T_{J}$	-40 to +125	°C
Storage Temperature Range		$T_{stg}$	-40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### **Thermal Characteristics**

Rating		Symbol	Value	Unit
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R <sub>ejc</sub> R <sub>eja</sub>	2.2 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds		$T_{\scriptscriptstyleL}$	260	°C

# Electrical Characteristics - OFF (TJ = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T <sub>1</sub> = 25°C	I <sub>DRM</sub> ,	-	-	0.01	ma A
$(V_D = V_{DRM} = V_{RRM}; Gate Open)$	T <sub>J</sub> = 125°C	I	-	-	2.0	mA

# Electrical Characteristics - ON (TJ = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Max	Unit
Peak On–State Voltage (Note 2) ( $I_{TM} = \pm 17 \text{ A}$ )		$V_{TM}$	-	1.85	V
Gate Trigger Current	MT2(+), G(+)		10	50	
(Continuous dc)	MT2(+), G(-)	I <sub>gt</sub>	10	50	mA
$(V_D = 12 \text{ V}, R_L = 100 \Omega)$	MT2(-), G(-)		10	50	
Holding Current ( $V_D = 12 \text{ V}$ , Gate Open, Initiating Current = $\pm 150 \text{ mA}$ ))		I <sub>H</sub>	-	60	mA
Latching Current $(V_D = 12 \text{ V, } I_C = 50 \text{ mA})$	MT2(+), G(+)	IL	_	60	mA V
	MT2(+), G(-)		_	80	
( ) ( ) ( ) ( ) ( ) ( ) ( ) ( ) ( ) ( )	MT2(-), G(-)		_	60	
· · · ·	MT2(+), G(+)	V <sub>GT</sub>	0.5	1.5	
Gate Trigger Voltage $(V_D = 12 \text{ V}, R_I = 100 \Omega)$	MT2(+), G(-)		0.5	1.5	
, p , f	MT2(-), G(-)		0.5	1.5	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Indicates Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%



<sup>1.</sup> V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

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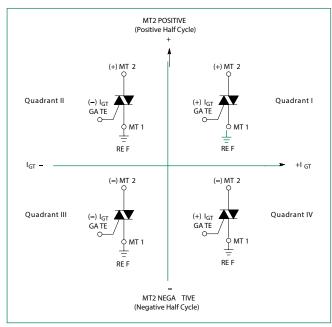
### **Dynamic Characteristics**

Characteristic	Symbol	Min	Тур	Max	Unit
Rate of Change of Commutating Current See Figure 10. ( $V_D = 400  \text{V},  I_{TM} = 4.4  \text{A}$ , Commutating dv/dt = 18 V/µs,Gate Open, $T_J = 125  ^{\circ}\text{C}$ , f = 250 Hz, with Snubber) $C_L = 10  \mu\text{F}  L_L = 40  \text{mH}$	(di/dt) <sub>c</sub>	15	-	_	A/ms
Critical Rate of Rise of Off-State Voltage ( $V_D$ = Rated $V_{DRM}$ , Exponential Waveform, $R_{GK}$ = 510 $\Omega$ , $T_J$ = 125°C)	dV/dt	600	_	_	V/µs
Repetitive Critical Rate of Rise of On-State Current IPK = 50 A; PW = 40 μsec; diG/dt = 200 mA/μsec; f = 60 Hz	di/dt	_	-	10	A/µs

### **Voltage Current Characteristic of SCR**

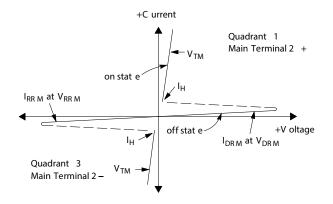
Symbol	Parameter
$V_{DRM}$	Peak Repetitive Forward Off State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
$V_{RRM}$	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
$V_{TM}$	Maximum On State Voltage
I <sub>H</sub>	Holding Current

#### **Quadrant Definitions for a Triac**



All polarities are referenced to MT1.

With in – phase signals (using standard AC lines) quadrants I and III are used



Surface Mount - 400V - 800V

Figure 1. Typical Gate Trigger Current vs Junction Temperature

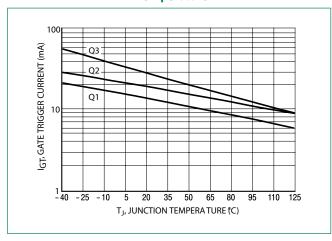


Figure 3. Typical Holding Current vs Junction Temperature

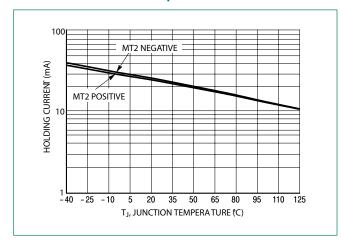


Figure 5. Typical RMS Current Derating

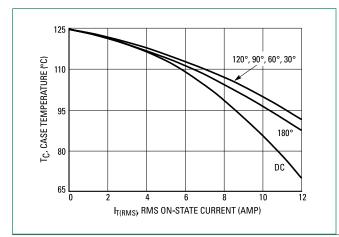


Figure 2. Typical Gate Trigger Voltage vs Junction Temperature

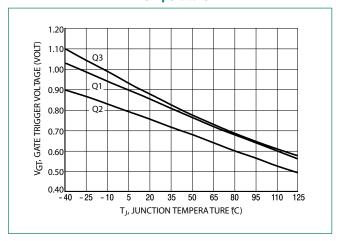
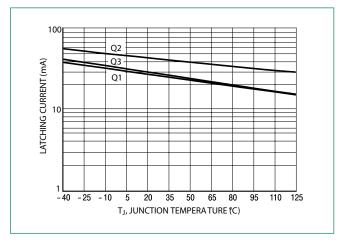
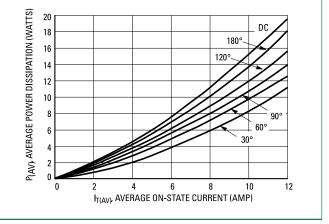


Figure 4. Typical Latching Current vs Junction Temperature



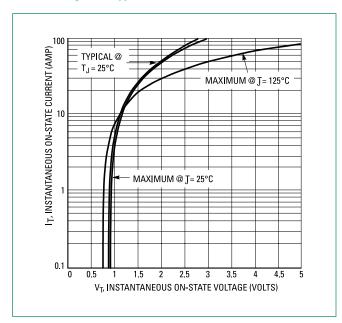
**Figure 6. On-State Power Dissipation** 



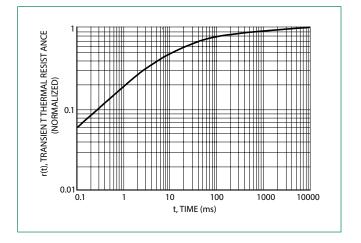


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**Figure 7. Typical On-State Characteristics** 



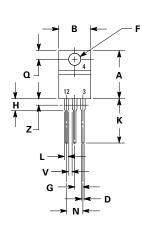
**Figure 8. Typical Thermal Response** 

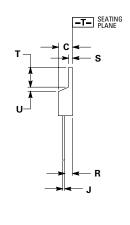




Surface Mount – 400V - 800V

#### **Dimensions**





#### **Part Marking System**





x =D, M, or N Y = Year

Y =Year M =Month

A =Assembly Site

XX =Lot Serial Code

G =Pb-Free Package

D:	Inches		Millimeters			
Dim	Min	Max	Min	Max		
Α	0.590	0.620	14.99	15.75		
В	0.380	0.420	9.65	10.67		
С	0.178	0.188	4.52	4.78		
D	0.025	0.035	0.64	0.89		
F	0.142	0.147	3.61	3.73		
G	0.095	0.105	2.41	2.67		
Н	0.110	0.130	2.79	3.30		
J	0.018	0.024	0.46	0.61		
K	0.540	0.575	13.72	14.61		
L	0.060	0.075	1.52	1.91		
N	0.195	0.205	4.95	5.21		
Q	0.105	0.115	2.67	2.92		
R	0.085	0.095	2.16	2.41		
S	0.045	0.060	1.14	1.52		
T	0.235	0.255	5.97	6.47		
U	0.000	0.050	0.00	1.27		
V	0.045		1.15			
Z		0.080		2.04		

Pin Assignment			
1	Main Terminal 1		
2	Main Terminal 2		
3	Gate		
4	No Connection		

### **Ordering Information**

Device	Package	Shipping		
MAC12HCDG				
MAC12HCMG	TO-220AB (Pb-Free)	1000 Units / Box		
MAC12HCNG	(151100)			



<sup>1.</sup> Dimensioning and tolerancing per ansi y14.5m, 1982.

Controlling dimension: inch.
 Dimension z defines a zone where all body and lead irregularities are allowed.

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### Littelfuse:

MAC12HCNG MAC12HCMG MAC12HCDG